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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/336,401	06/18/1999	JULIA S. SVIRCHEVSKI	LAM1P109	7588

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EXAMINER

UMEZ ERONINI, LYNETTE T

ART UNIT	PAPER NUMBER
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1765

DATE MAILED: 09/22/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/336,401

Applicant(s)

SVIRCHEVSKI ET AL

Examiner

Lynette T. Umez-Eronini

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 30 June 2003.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-31 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-31 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____.
- 4) ☐ Interview Summary (PTO-413) Paper No(s) _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

3. Claims 1, 4, 5 and 9-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bersin (US 5,882,489) in view of Gockel et al. (US 5,809,832) and further in view of Tadokoro (US 4,559,718).

As pertaining to claims 1, 4, 5, and 9-11, Bersin teaches a method of cleaning a surface of a semiconductor wafer following a plasma etching operation. The method comprises rinsing the wafer in DI water, optionally with ultrasonic agitation (column 4, lines 22-27), which is the same as using a non-splash rinse technique wherein the non-

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splash rinse technique being configured to quickly and evenly saturate the surface of the semiconductor wafer.

Bersin differs in failing to teach scrubbing the surface of the semiconductor wafer with a cleaning brush that applies a chemical solution to the surface of the wafer, **in claim 1** and wetting and scrubbing in a brush box, **in claim 4**.

Gockel teaches, "A wet processing system such as the scrubber described above comprises several distinct stations or modules. Each module is typically enclosed in a box-like structure which comprises the appropriate processing apparatus for that station. For example, a scrubber may comprise a load or send station, one or more scrub stations, a spin rinse and spin dry station, . . ." (column 1, lines 21-28). "A scrub station typically comprises one or more brushes, . . . during scrubbing and sprays or nozzles for dispensing chemicals" (column 1, lines 39-42). "Each brush includes multiple protrusions . . . to facilitate the cleaning of wafers. . . . the upper and lower brushes are configured to provide fluid (same as chemical) to the core of the brush to be dispersed to the . . . brush surface," (column 8, lines 13-17). The aforementioned, reads on, scrubbing the surface of a wafer with a cleaning brush that applies a chemical solution to the surface of the wafer after the wetting, as in claim 1. Gockel further teaches, "In brush 1 station **1420**, a dirty wafer **1402**, is brushed and sprayed . . ." (column 15, lines 3-6) and " . . . incorporating spray heads **505** and **506** to spray cleaning solutions . . . onto the wafer . . ." (column 7, lines 50-53 and Figure 5), which reads on setting a first delivery and a second delivery source over the surface of the

wafer in order to wet the surface of the wafer with a flow rate of water and further reads on, performing the wetting and scrubbing in a brush box, as in claim 4.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Bersin by using the scrubbing method as taught by Gockel for the purpose of removing wafer contaminants that may cause device failure.

Bersin in view of Gockel differs in failing to teach keeping the wafer substantially dry, **in claim 1**.

Tadokoro teaches, “. . . a method . . . for drying a semiconductor wafer, is capable of drying the wafers in a perfect manner while keeping them clean, thereby enhancing the quality of the dried wafers” (column 1, lines 32-36), which reads on keeping the semiconductor wafer substantially dry.

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Bersin in view of Gockel by using Tadokoro's method of drying a semiconductor wafer for the purpose of enhancing the quality of the dried wafers (Tadokoro, column 1, lines 32-36).

4. Claims 6 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bersin (US '489) in view of Gockel (US '832) and Tadokoro (US '718) as applied to claim 1 above and further in view of Elliot et al. (US 5,669,979).

Bersin in view of Gockel and Tadokoro differs in failing to teach setting flow rate between 50 ml/minute and 500 ml/minute, **in claim 6** and setting a time of less than 4 seconds to wet substantially all of a top surface of the wafer, **in claim 8**.

Elliot teaches surface cleaning semiconductor substrate using a liquid that has a velocity between 0.2 mm/sec and 2,000 mm/sec (column 1, lines 11-25 and column 2, lines 9-12 and 28-30). Elliot's flow rate, which is reported in terms of a velocity, provides evidence that the flow rate as well as setting of time is a so-called "result effective variable."

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Bersin in view of Gockel and Tadokoro by employing Elliot's flow rate, since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

5. Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Bersin (US '678) in view of Gockel (US ') and Tadokoro (US '718) as applied to claim 1 above and further in view of Tomoeda et al. (5,759,614).

Bersin in view of Gockel and Tadokoro differs in failing to teach rotating the semiconductor wafer about a radial axis at a rate of between about 2 revolutions per minute and about 20 revolutions per minute.

Tomoeda teaches supplying a rinse solution onto a wafer having a rotational speed of 1.5 to 2.0 rpm (column 8, lines 5-7), which falls in applicant's range of 2 to about 20 revolutions per minute and which provides evidence the range of the rotational speed is a so-called "result effective variable."

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Bersin in view of

Gockel and Tadokoro by employing using Tomoeda's rotational speed, which is a so-called "result effective variable," since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

6. Claims 21-24 rejected under 35 U.S.C. 103(a) as being unpatentable over Lo et al. (US 5,804,091) and further in view of Gabriel (US 5,730,834).

As pertaining to claim 21, Lo teaches a method of cleaning a surface of a semiconductor wafer following a plasma etching operation. The cleaning method comprises: water flushing with megasonic shaking to clean the wafer surface (Abstract; column 1, lines 39-52; column 2, lines 3-34; column 7, lines 50-53 and Figure 5), which is the same as wetting the surface of the semiconductor wafer by using a non-splash rinse technique. Using Lo's method of cleaning a wafer surface in the same manner as the claimed invention would result in the non-splash rinse technique being configured to quickly and evenly saturate the surface of the semiconductor wafer. Lo's method further reads on, applying liquid to the surface of the semiconductor wafer through the outlet end of the at least one delivery source. Lo's plasma etching operation is described as a conventional process that is used in making tungsten plug (column 1, lines 13-36) and is called tungsten etch back (column 2, lines -13), which is the same as the plasma etching operation is a tungsten etch-Back (WEB) operation, **as in claim 24.**

Lo differs in failing to teach setting an outlet end of at least one delivery source over the surface of the semiconductor wafer at an angle in a range from about 5

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degrees to about 35 degrees relative to the surface of the wafer, **in claim 21**; setting the outlet end of the at least one delivery source to overlie and edge of the semiconductor wafer by a distance in a range from about 2 mm to about 30 mm, **in claim 22**; and applying deionized wafer at a flow rate between 50ml/minute and about 300 l/minute, **in claim 23**.

Elliot teaches a method of cleaning a surface and the depth of substrate surface below the surface of the liquid may be less than 50 mm, and preferably less than 20 mm (column 2, lines 13-15), which lies within applicant's range from 2 mm to about 30 mm. The fluid may be a gas or liquid directed at an angle of less than 90 degrees to the surface, preferably between 0 and 20 degrees (column 2, lines 18-21 and 27-30), which falls within applicant's range from about 5 to 35 degrees. Elliot also teaches surface cleaning semiconductor substrate using a liquid that has a velocity between 0.2 mm/sec and 2,000 mm/sec (column 1, lines 11-25 and column 2, lines 9-12 and 28-30). Elliot's flow rate, which is reported in terms of a velocity, provides evidence that the flow rate as well as the range of the angle at which the fluid (delivery source) is directed to the wafer surface and range of distance at which the fluid (delivery source) overlies the wafer, are so-called "result effective variables."

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Lo by employing Elliot's angles, depths, and flow rates, which have been shown to be "result effective variables" since it has been held that discovering an optimum value of a result effective

variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Lo in view of Elliot differs in failing to teach scrubbing the surface of the semiconductor wafer with a cleaning brush that applies a chemical solution to the surface of the wafer, **in claim 21**

Gockel teaches, "A scrub station typically comprises one or more brushes, . . . during scrubbing and spray or nozzles for dispensing chemicals" (column 1, lines 39-42).

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Lo in view of Elliot by using the scrubbing method as taught by Gockel for the purpose of removing wafer contaminants that may cause device failure.

7. Claims 25-31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Gockel (US '832) in view of Tadokoro (US '718) and further in view of Elliot (US '979).

Gockel teaches a method for cleaning the surface of semiconductor wafers. The method comprises: loading and moving dirty wafers from load station to from load station to scrubber (column 14, lines 60-64 and Figure **14**), which reads on,

receiving a semiconductor wafer.

Gockel teaches, incorporating spray heads **505 and 506** that are mounted at the entrance and exit of brush boxes **105 and 106** to spray cleaning solution onto wafers (column 7, lines 51-53 and Figure **5**), which reads on,

positioning an outlet end of at least one liquid delivery source relative to a surface of the semiconductor wafer so that the outlet end overlies an edge of the semiconductor wafer and applying liquid to the surface of the semiconductor wafer through the outlet end of the at least one liquid delivery source.

Gockel differs in failing to teach, the semiconductor wafer being substantially dry.

Tadokoro teaches, "a method . . . for drying a semiconductor wafer, which is capable of drying the wafers in a perfect manner while keeping them clean, thereby enhancing the quality of the dried wafers" (column 1, lines 32-36), which read on keeping the semiconductor wafer substantially dry.

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Gockel by using Tadokoro's method of drying a semiconductor wafer for the purpose of enhancing the quality of the dried wafers (Tadokoro, column 1, lines 32-36).

Gockel in view of Tadokoro differs in failing to teach specify processing variables such as a distance from about 2 mm to about 30 mm from where the delivery source overlies an edge of the semiconductor wafer; an angle in a range from 5-35 degrees of the outlet end of the liquid delivery source relative to the wafer surface, the distance of 2 to 15 mm from where the outlet end is disposed above the surface of the semiconductor wafer, **in claims 25**; flow rate between 50 ml/minute and 300 ml/minute through the outlet end of the liquid delivery source, **in claim 27**; a distance from about 5 mm from the outlet end of the delivery source that overlies an edge of the semiconductor wafer, **in claim 29**; an angle of 15 degrees is oriented from the outlet end of the delivery

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source relative to the surface of the semiconductor wafer, **in claim 30**; and a distance about 7 mm from outlet end of the delivery source that is disposed above the surface of the semiconductor wafer, **in claim 31**.

Elliot teaches the depth of substrate surface below the surface of the liquid may be less than 50 mm, and preferably less than 20 mm (column 2, lines 13-15), which lies within applicant's range from 2 mm to about 30 mm. The fluid may be a gas or liquid directed at an angle of less than 90 degrees to the surface, preferably between 0 and 20 degrees (column 2, lines 18-21 and 27-30), which falls within 5 to 35 degrees, as in the claimed invention. Elliot also teaches surface cleaning semiconductor substrate using a liquid that has a velocity between 0.2 mm/sec and 2,000 mm/sec (column 1, lines 11-25 and column 2, lines 9-12 and 28-30). Elliot's flow rate, which is reported in terms of a velocity, provides evidence that the flow rate as well as the range of the angle at which the fluid (delivery source) is directed to the wafer surface and the range of distance at which the fluid (delivery source) overlies the wafer, are so-called "result effective variables."

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Lo by employing using Elliot's angles, depths, and flow rates, which have been shown to be a so-called "result effective variable," since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

8. Claim 28 is rejected under 35 U.S.C. 103(a) as being unpatentable over Gockel (US ') in view of Tadokoro (US '718) and Elliot (US '979) as applied to claim 25 above, and further in view of Tomoeda ('614).

Gockel in view of Tadokoro and Elliot differ in failing to teach the semiconductor is rotated about a radial axis at a rate of about 2 revolutions per minute to about 20 revolutions per minute.

Tomoeda teaches supplying a rinse solution onto a wafer having a rotational speed of 1.5 to 2.0 rpm (column 8, lines 5-7), which falls within applicant's range of 2 to about 20 revolutions per minute and which provides evidence the range or the rotational speed is a so-called "result effective variable."

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Gockel in view of and Tadokoro and Elliot by employing Tomoeda rotational speed, which is a so-called "result effective variable," since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Response to Arguments

9. Applicant's arguments with respect to claims 1-31 have been considered but are moot in view of the new ground(s) of rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 703-306-9074. The examiner is normally unavailable on the First Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 703-305-2667. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Lynette T. Umez-Eronini
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September 13, 2003